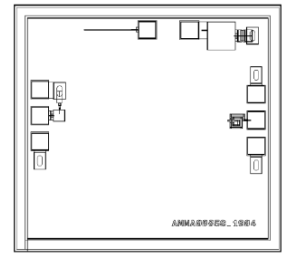


AMT1102
6 – 16GHz Power Amplifier Chip



Key Features :

- Frequency range : 6 – 16GHz
- Typical small signal Gain : 24dB
- Typical output power : 22.5dBm
- Voltage bias : +5V, 0.13A
- Chip dimensions : 1.47mm x 1.35mm x 0.1mm
- Applications : wireless communication, transceiver module, radio telecommunication etc.

Description :

AMT1102 chip is a Gallium Arsenide (GaAs) pHEMT process designed power amplifier chip, with a wide frequency range of 6 – 16GHz, single voltage operation, drain voltage Vds at 5V, linear gain of 24dB, saturated output power at 22.5dBm. This chip is designed with ground through metal vias on the back technology. All chip products p are 100% RF tested.

Absolute Maximum Ratings (Ta = 25°C)

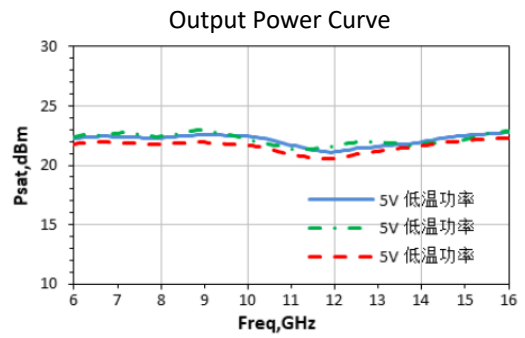
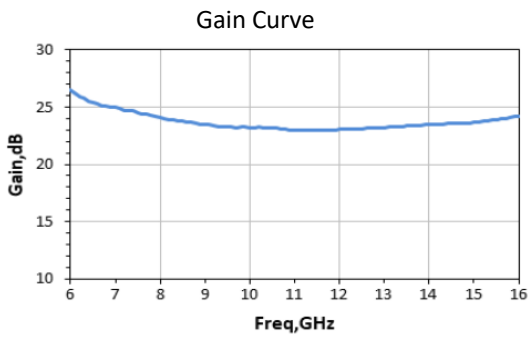
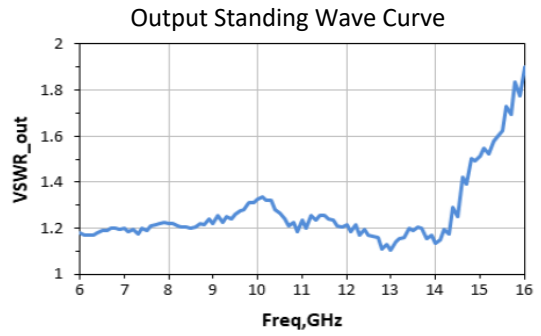
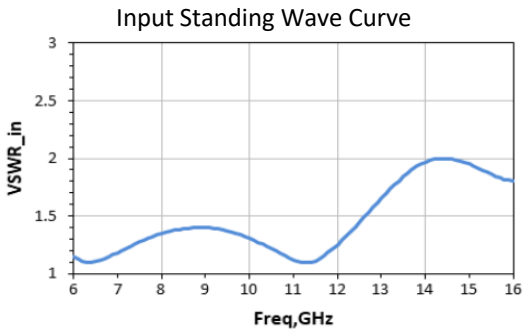
Symbol	Parameter	Value	Remark
Vd	Drain voltage	+11V	
Pin	Input Signal Power	15dBm	
Tch	Operating Temperature	-55 ~ +125°C	
Tm	Sintering Temperature	310°C	30s, N ₂ protection
Tstg	Storage Temperature	-65 ~ +150°C	

[1] Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

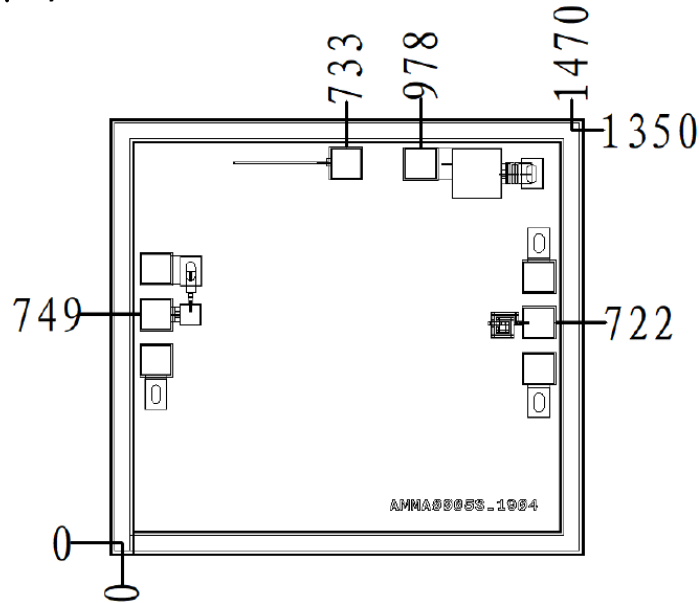
Electrical Characteristics (Ta = 25°C)

Symbol	Parameter	Test Condition	Value			Unit
			Min	Typical	Max	
G	Small Signal Gain	Vd = 5V F : 6-16GHz	22	24	-	dB
Id	Drain Current		-	130	-	mA
VSWR_in	Input SW		-	1.8	-	
VSWR_out	Output SW		-	1.8	-	
Gp	Power Gain	Vd = 5V F : 6-16GHz Duty Cycle : 20%	-	17.5	-	dB
Po(sat)	Saturated Output Power		22	22.5	-	dBm

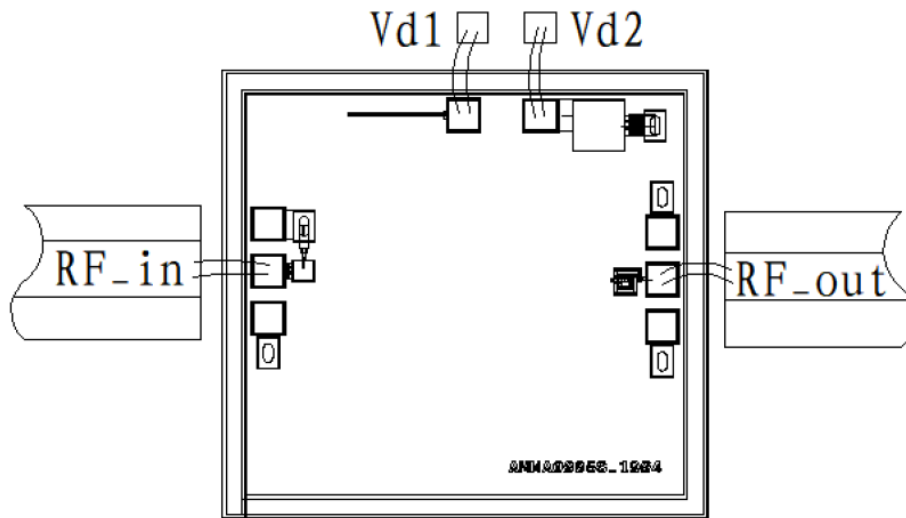
Typical Performance



Chip Dimensions (Unit : μm)



Chip Layout Diagram



Pad Definition

Symbol	Function	Dimension	Equivalent Circuit
RF_in	RF signal input port, connecting to external 50 Ω system. DC blocking capacitor is needed, if external DC current is applied to this pad.	100*100 μm^2	
RF_out	RF signal output port, connecting to external 50 Ω system, no need to add DC blocking capacitor.	100*100 μm^2	
Vd1	Amplifier drain bias, need external 100pF, 1000pF capacitor.	100*100 μm^2	
Vd2	Amplifier drain bias, need external 100pF, 1000pF capacitor.	106*100 μm^2	

Refer to Appendix A for details